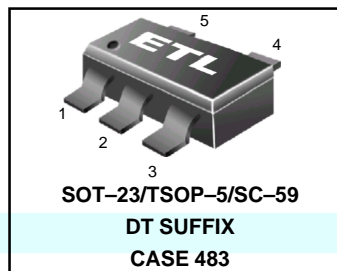
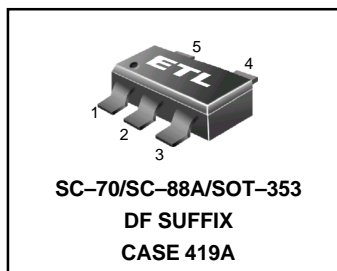


## 2-Input NAND Gate

**MC74VHC1G00**

The MC74VHC1G00 is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation. The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The MC74VHC1G00 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G00 to be used to interface 5 V circuits to 3 V circuits.

- High Speed:  $t_{PD} = 3.0 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \text{ mA}$  (Max) at  $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families



### MARKING DIAGRAMS

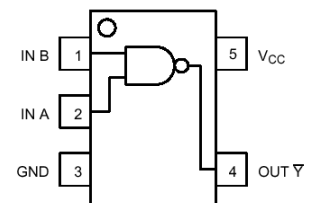
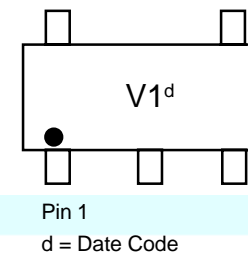
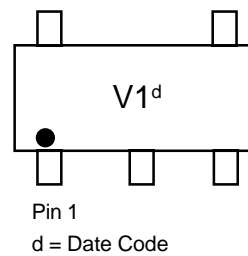


Figure 1. Pinout (Top View)

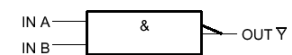


Figure 2. Logic Symbol

PIN ASSIGNMENT	
1	IN B
2	IN A
3	GND
4	OUT $\bar{Y}$
5	$V_{CC}$

### FUNCTION TABLE

Inputs		Output
A	B	$\bar{Y}$
L	L	H
L	H	H
H	L	H
H	H	L

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

**MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V
V <sub>IN</sub>	DC Input Voltage	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>OUT</sub>	DC Output Voltage	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>OUT</sub>	DC Output Sink Current	± 12.5	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin	± 25	mA
T <sub>STG</sub>	Storage Temperature Range	- 65 to + 150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T <sub>J</sub>	Junction Temperature Under Bias	+ 150	°C
θ <sub>JA</sub>	Thermal Resistance	SC-70/SC-88A (Note 1)	150 °C/W
		TSOP-5	200
P <sub>D</sub>	Power Dissipation in Still Air at 85C	SC-70/SC-88A	150 mW
		TSOP-5	230
MSL	Moisture Sensitivity	Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 (0.125 in)
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2)	>2000 V
		Machine Model (Note 3)	> 200
		Charged Device Model (Note 4)	N/A
I <sub>LATCH-UP</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 85C (Note 5)	± 500 mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0.0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 3.3 ± 0.3 V	0	100 ns/V
		V <sub>CC</sub> = 5.0 ± 0.5 V	0	20

**DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES**

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

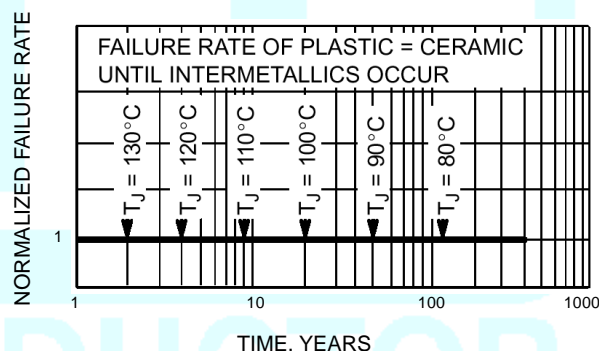


Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		-55°C to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0	1.5			1.5		1.5		V
			3.0	2.1		2.1		2.1			
			4.5	3.15		3.15		3.15			
			5.5	3.85		3.85		3.85			
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0			0.5		0.5		0.5	V
			3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -50 μA	2.0	1.9	2.0		1.9		1.9		V
			3.0	2.9	3.0		2.9		2.9		
			4.5	4.4	4.0		4.4		4.4		
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -4 mA I <sub>OH</sub> = -8 mA	3.0	2.58			2.48		2.34		
			4.5	3.94			3.80		3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	2.0		0.0	0.1		0.1		0.1	V
			3.0		0.0	0.1		0.1		0.1	
			4.5		0.0	0.1		0.1		0.1	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0			0.36		0.44		0.52	
			4.5			0.36		0.44		0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS C<sub>load</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 3.0 ns

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> ≤ 85°C		-55°C ≤ T <sub>A</sub> ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to $\bar{Y}$	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF		4.5	7.9		9.5		11.0	ns
		C <sub>L</sub> = 50 pF		5.6	11.4		13.0		15.1	
		V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF		3.0	5.5		6.5		8.0	
		C <sub>L</sub> = 50 pF		3.8	7.5		8.5		10.0	
C <sub>IN</sub>	Maximum Input Capacitance			5.5	10		10		10	pF
			<b>Typical @ 25°C, V<sub>CC</sub> = 5.0 V</b>							
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)		10					pF		

6. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

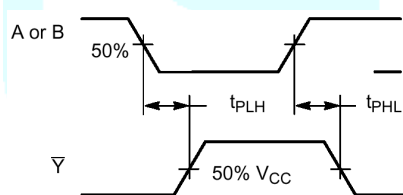


Figure 4. Switching Waveforms

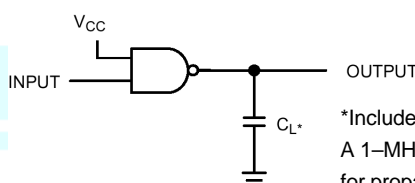


Figure 5. Test Circuit

\*Includes all probe and jig capacitance.  
A 1-MHz square input wave is recommended for propagation delay tests.

## MC74VHC1G00

### DEVICE ORDERING INFORMATION

Device Order Number	Device Nomenclature						Package Type (Name/SOT#/Common Name)	Tape and Reel Size
	Logic Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix		
MC74VHC1G00DFT	MC	74	VHC1G	00	DF	T1	SC-70/SC-88A/ SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G00DFT2	MC	74	VHC1G	00	DF	T2	SC-70/SC-88A/ SOT-353	178 mm (7 in) 3000 Unit
MC74VHC1G00DTT1	MC	74	VHC1G	00	DT	T1	SOT-23/TSOP-5/ SC-59	178 mm (7 in) 3000 Unit

